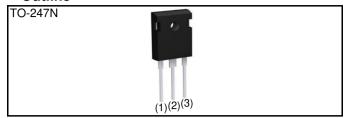


Automotive Grade N-channel SiC power MOSFET

V _{DSS}	1200V
R _{DS(on)} (Typ.)	105mΩ
I _D ^{*1}	24A
P_D	134W

Outline

●Inner circuit



(2)

(**3**)

(1) Gate (2) Drain

(3) Source

*Body Diode

Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating; RoHS compliant

Application

- Automobile
- Switch mode power supplies

Packaging specifications

ging specimoations	
Packing	Tube
Reel size (mm)	-
Tape width (mm)	-
Basic ordering unit (pcs)	30
Taping code	C11
Marking	SCT3105KL
	Reel size (mm) Tape width (mm) Basic ordering unit (pcs) Taping code

● **Absolute maximum ratings** (T_{vi} = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DSS}	1200	V
Continuous Drain current	$T_c = 25^{\circ}C$	I _D *1	24	Α
Continuous Drain current	T _c = 100°C	I _D *1	17	Α
Pulsed Drain current(T _c = 25°C)		I _{D,pulse} *2	60	Α
Gate - Source voltage (DC)		V_{GSS}	-4 to +22	V
Gate - Source surge voltage (t _{surge} < 300nsec)		$V_{\rm GSS_surge}^{*3}$	-4 to +26	V
Recommended drive voltage		$V_{\mathrm{GS_op}}^{}^{*4}}$	0 / +18	V
Virtual Junction temperature		T _{vj}	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Electrical characteristics (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
- aramotor	Symbol	Conditions	Min.	Тур.	Max.	Offic
		$V_{GS} = 0V$, $I_D = 1mA$				
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$T_{vj} = 25^{\circ}C$	1200	-	-	V
· o.ta.go		$T_{vj} = -55^{\circ}C$	1200	-	-	
		$V_{GS} = 0V, V_{DS} = 1200V$				
Zero Gate voltage Drain current	I _{DSS}	$T_{vj} = 25^{\circ}C$	-	1	10	μΑ
Drain Garrein		T _{vj} = 150°C	-	2	-	
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V$, $V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -4V$, $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_D = 3.81 \text{mA}$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 7.6A$				
Static Drain - Source on - state resistance	R _{DS(on)} *5	$T_{vj} = 25^{\circ}C$	-	105	137	mΩ
		T _{vj} = 150°C	-	179	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	13	-	Ω

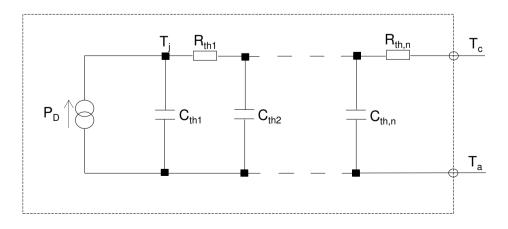
Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-	0.86	1.12	K/W

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	1.08E-01	
R _{th2}	3.73E-01	K/W
R _{th3}	3.41E-01	

Symbol	Value	Unit
C _{th1}	4.72E-04	
C _{th2}	3.97E-03	Ws/K
C _{th3}	1.31E-02	



ullet Electrical characteristics ($T_{vj} = 25^{\circ}\text{C}$ unless otherwise specifi

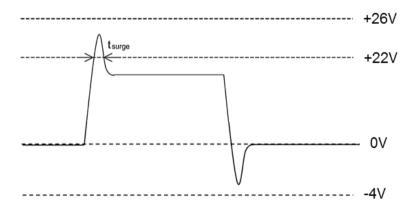
Doromotor	Symbol	Conditions		Values		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Transconductance	${g_{fs}}^{*5}$	$V_{DS} = 10V, I_D = 7.6A$	-	3.4	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	574	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	59	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	28	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$ $V_{DS} = 0V \text{ to } 600V$	-	159	-	pF
Total Gate charge	Q_g^{*5}	$V_{DS} = 600V$ $I_{D} = 7.6A$	-	51	-	
Gate - Source charge	Q _{gs} *5	$V_{GS} = 18V$	-	10	-	nC
Gate - Drain charge	Q _{gd} *5	See Fig. 1-1.	-	25	-	
Turn - on delay time	t _{d(on)} *5	V _{DS} = 400V	-	17	-	
Rise time	t _r *5	$I_D = 7.6A$ $V_{GS} = 0V/+18V$	-	27	-	
Turn - off delay time	t _{d(off)} *5	$R_G = 0\Omega$ $R_L = 53\Omega$	-	31	-	ns
Fall time	t _f *5	See Fig. 1-1, 1-2.	-	17	-	
Turn - on switching loss	E _{on} *5	$V_{DS} = 600V$ $V_{GS} = 0V/18V$, $I_{D} = 7.6A$ $R_{G} = 0\Omega$, $L = 750\mu H$	-	159	-	1
Turn - off switching loss	E _{off} *5	E_{on} includes diode reverse recovery L_{σ} = 50nH, C_{σ} = 200pF See Fig. 2-1, 2-2.	-	2	-	μJ

●Body diode electrical characteristics (Source-Drain) (T_{vj} = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Body diode continuous, forward current	I _S *1	T _c = 25°C	-	i	24	Α
Body diode direct current, pulsed	I _{SM} *2	11 _c = 23 0	ı	i	60	Α
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_{S} = 7.6A$	ı	3.2	ı	V
Reverse recovery time	t _{rr} *5	$I_F = 7.6A$ $V_B = 600V$	ı	15	ı	ns
Reverse recovery charge	Q _{rr} *5	di/dt = 1100A/µs	ı	53	ı	nC
Peak reverse recovery current	: I _{rrm} *5	$L_{\sigma} = 50$ nH, $C_{\sigma} = 200$ pF See Fig. 3-1, 3-2.	-	6.5	-	Α

^{*1} Limited by maximum T_{vi} and for Max. R_{thJC} .

*3 Example of acceptable V_{GS} waveform



*5 Pulsed

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

 $^{^{*}4}$ Please be advised not to use SiC-MOSFETs with V_{GS} below 13V as doing so may cause thermal runaway.

20

0

25

•Electrical characteristic curves

160
140
140
[M] 120
40

60
40

Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

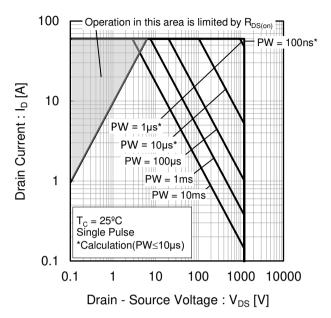


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

75

125

Case Temperature : T_C [°C]

175

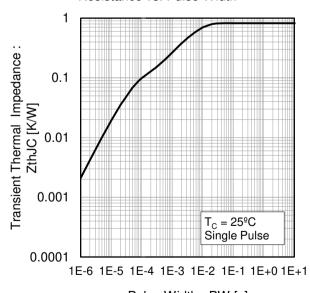


Fig.4 Typical Output Characteristics(I)

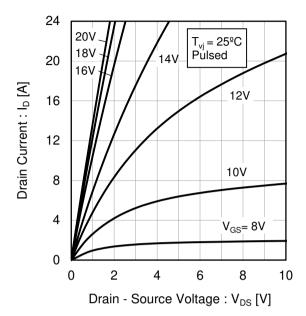


Fig.5 Typical Output Characteristics(II)

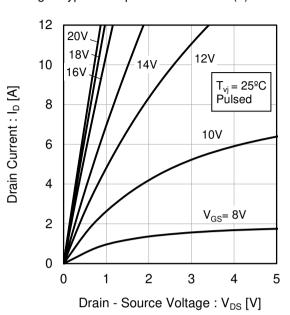
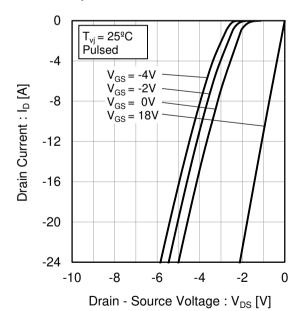
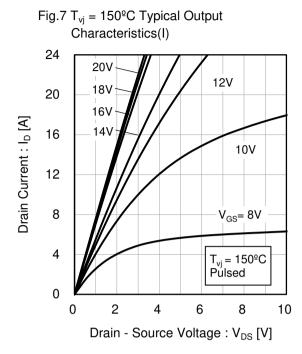


Fig.6 $T_{v_i} = 25^{\circ}C$ 3rd Quadrant Characteristics





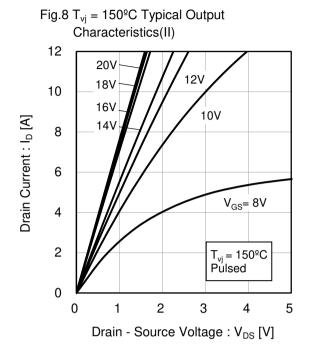


Fig.9 $T_{vj} = 150^{\circ}\text{C}$ 3rd Quadrant Characteristics

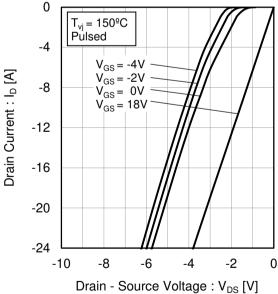


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage

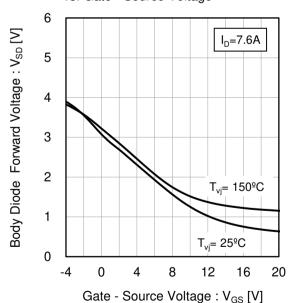


Fig.11 Typical Transfer Characteristics (I)

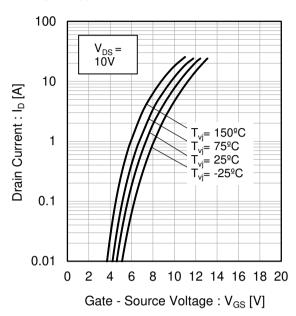


Fig.12 Typical Transfer Characteristics (II)

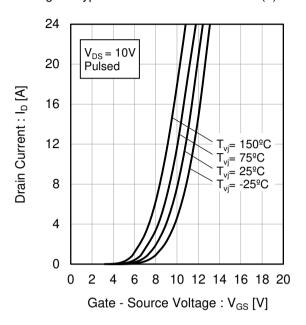


Fig.13 Gate Threshold Voltage vs. Junction Temperature

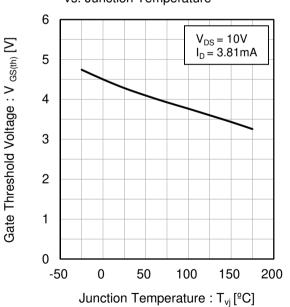
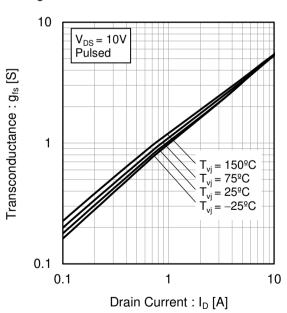


Fig.14 Transconductance vs. Drain Current



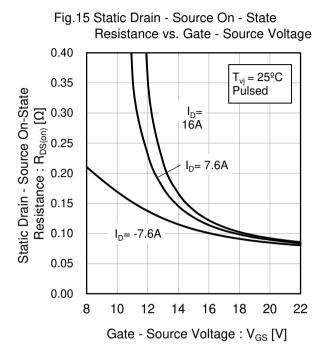


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature 0.30 $V_{GS} = 18V$ Pulsed Static Drain - Source On-State Resistance : $R_{DS(on)}[\Omega]$ 0.24 I_D= 16A 0.18 I_D= 7.6A 0.12 $I_{D} = -7.6A$ 0.06 0.00 0 100 200 -50 50 150 Junction Temperature : T_{vi} [°C]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current 1 Static Drain - Source On-State Resistance: $R_{DS(on)}\left[\Omega\right]$ 0.1 T_{vj} = 150ºC T_{vi} = 125ºC $T_{vj} = 75^{\circ}C$ $T_{vj}^{vj} = 25^{\circ}C$ $V_{GS} = 18V$ T_{vi} = −25ºC Pulsed 0.01 10 100 Drain Current: ID [A]

Voltage vs. Junction Temperature

1.04

1.03

1.00

1.01

1.01

1.00

1.00

1.00

0.99

0.98

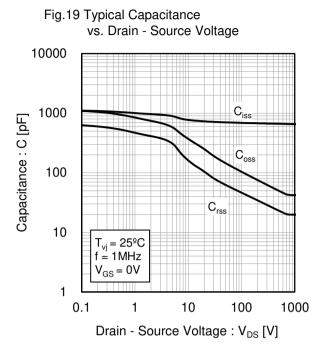
-50

0

Junction Temperature : T_{vi} [°C]

ROHM

Fig.18 Normalized Drain - Source Breakdown



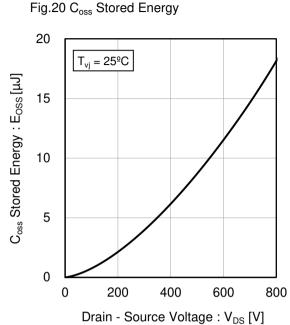
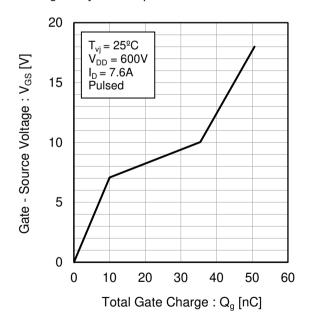


Fig.21 Dynamic Input Characteristics



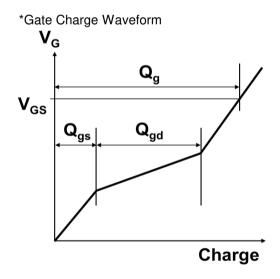


Fig.19 Typical Switching Time vs. Drain Current

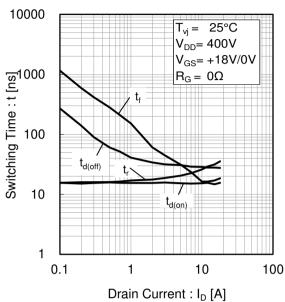


Fig.20 Typical Switching Loss vs. Drain - Source Voltage

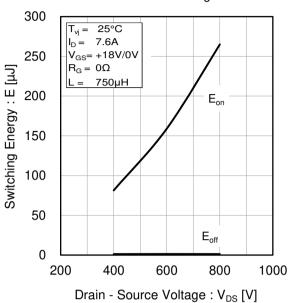


Fig.21 Typical Switching Loss vs. Drain Current

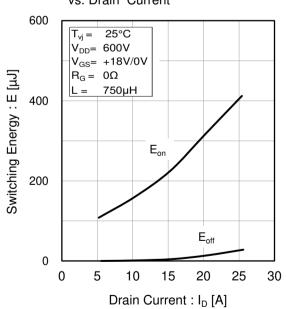
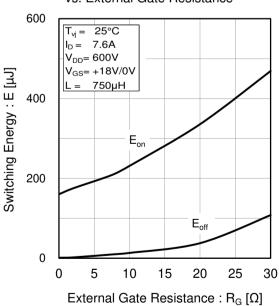


Fig.22 Typical Switching Loss vs. External Gate Resistance



Measurement circuits and waveforms

Fig.1-1 Gate Charge and Switching Time Measurement Circuit

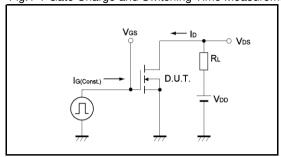


Fig.2-1 Switching Energy Measurement Circuit

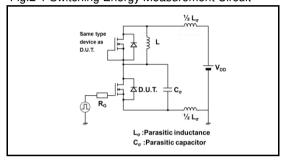


Fig.3-1 Reverse Recovery Time Measurement Circuit

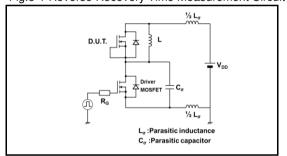


Fig.1-2 Waveforms for Switching Time

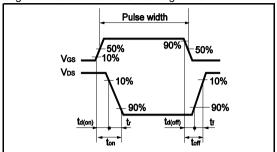


Fig.2-2 Waveforms for Switching Energy Loss

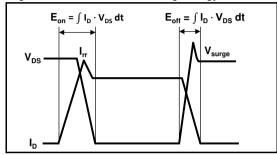
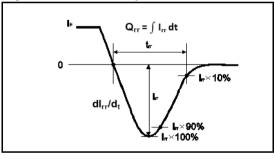
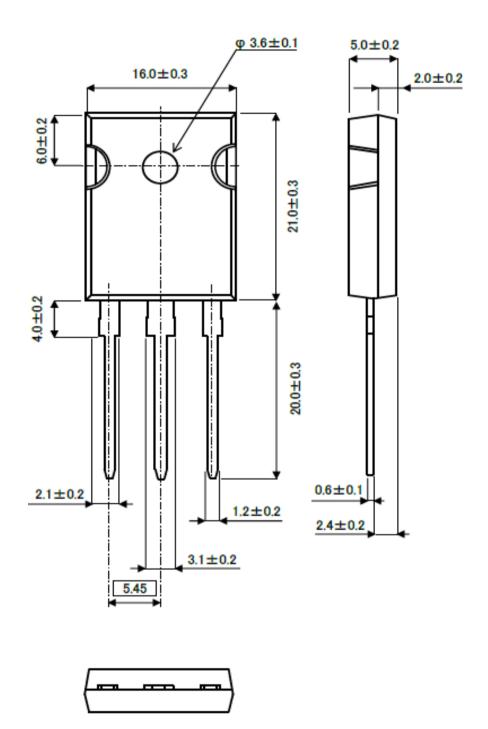


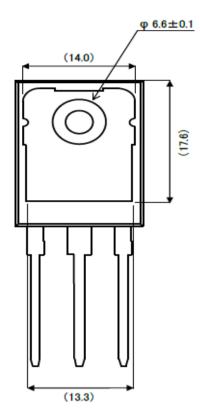
Fig.3-2 Reverse Recovery Waveform



●Package Dimensions

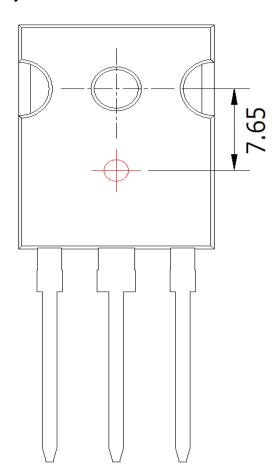


Unit: mm



Unit: mm

●Die Bonding Layout





- •Front view of the packaging.
- •Dimensions are design values.
- ·If the heat sink is to be installed, it should be in contact with the die bonding point.

Unit: mm

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